



TO-92 Plastic-Encapsulate Transistors

BC350 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

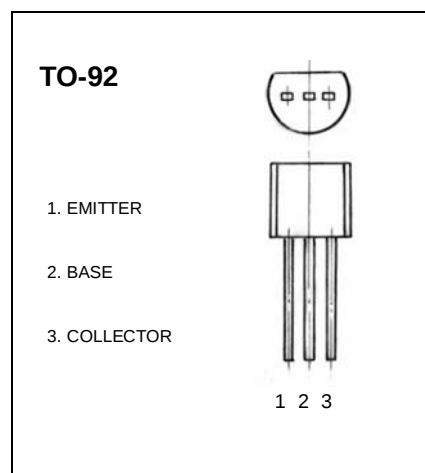
$$I_{CM}: -0.1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -35\text{V}, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	40		450	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -10\text{mA}, I_B = -1\text{mA}$			-0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -10\text{mA}, I_B = -1\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 30\text{MHz}$	125			MHz